

**SPECIFICATION AMENDMENTS**

Please amend paragraph [0010] beginning on page 4, line 25 with the following:

Accordingly, the invention is aimed to provide a substrate for growth of a nitride semiconductor capable of obtaining a high-quality nitride semiconductor crystal layer.

Please amend the title on page 7, line 16, of the specification to read as follows:

**BEST MADE MODE FOR CARRYING OUT THE INVENTION**